

**FEATURES**

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER  
P1dB= 40.5dBm at 13.75GHz to 14.5GHz
- HIGH GAIN  
G1dB= 5.5dB at 13.75GHz to 14.5GHz
- HERMETICALLY SEALED PACKAGE



**RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V IDSset= 4.0A f = 13.75 to 14.5GHz	dBm	40.0	40.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	4.5	5.5	—
Drain Current	IDS		A	—	4.5	5.5
Power Added Efficiency	$\eta_{add}$		%	—	20	—
Channel Temperature Rise	$\Delta T_{ch}$		(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—

**Recommended Gate Resistance(Rg): 100 Ω**

**ELECTRICAL CHARACTERISTICS ( Ta= 25°C )**

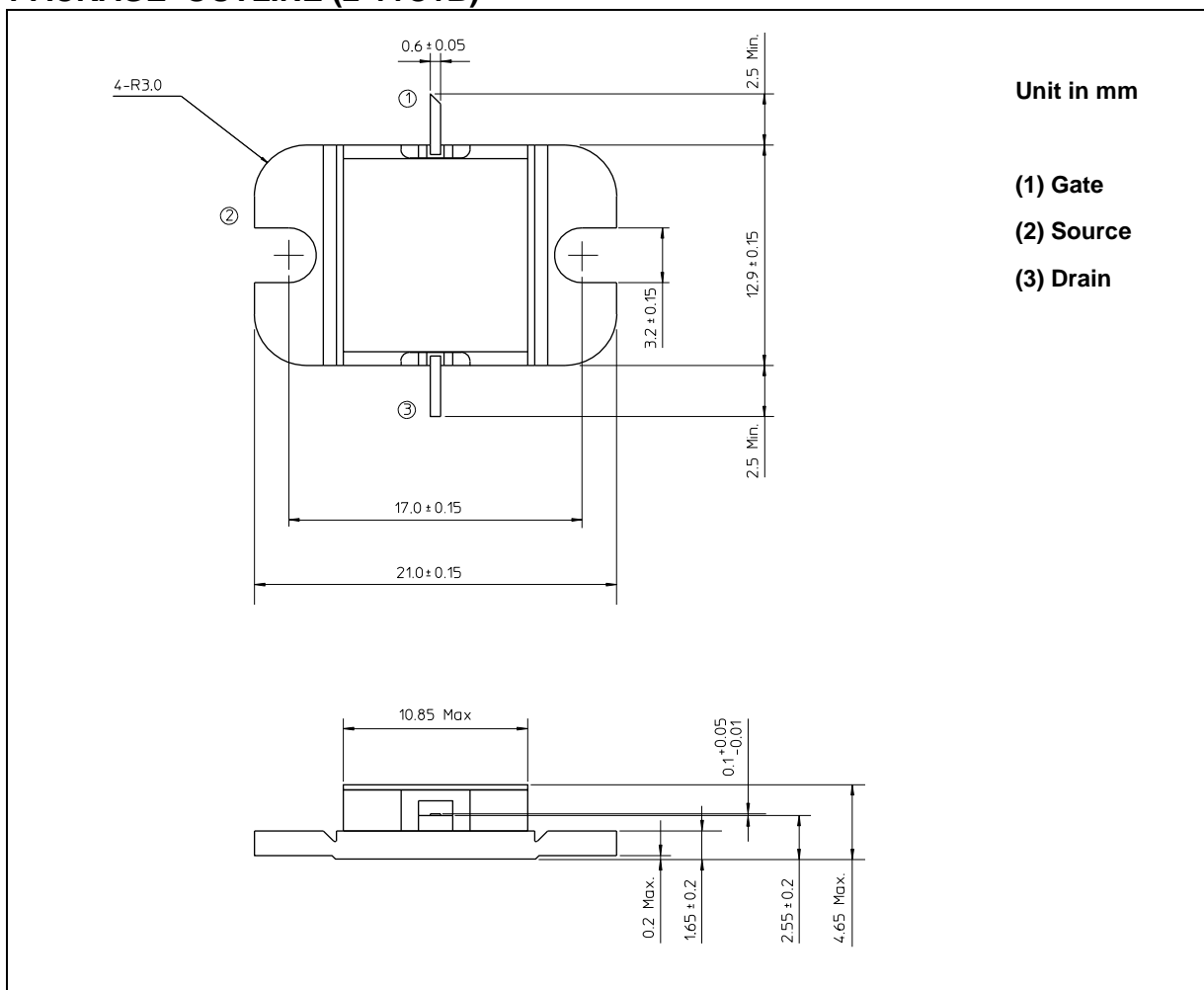
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	S	—	3.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-1.0	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -145μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

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**ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	11.5
Total Power Dissipation (Tc= 25°C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-11C1B)**

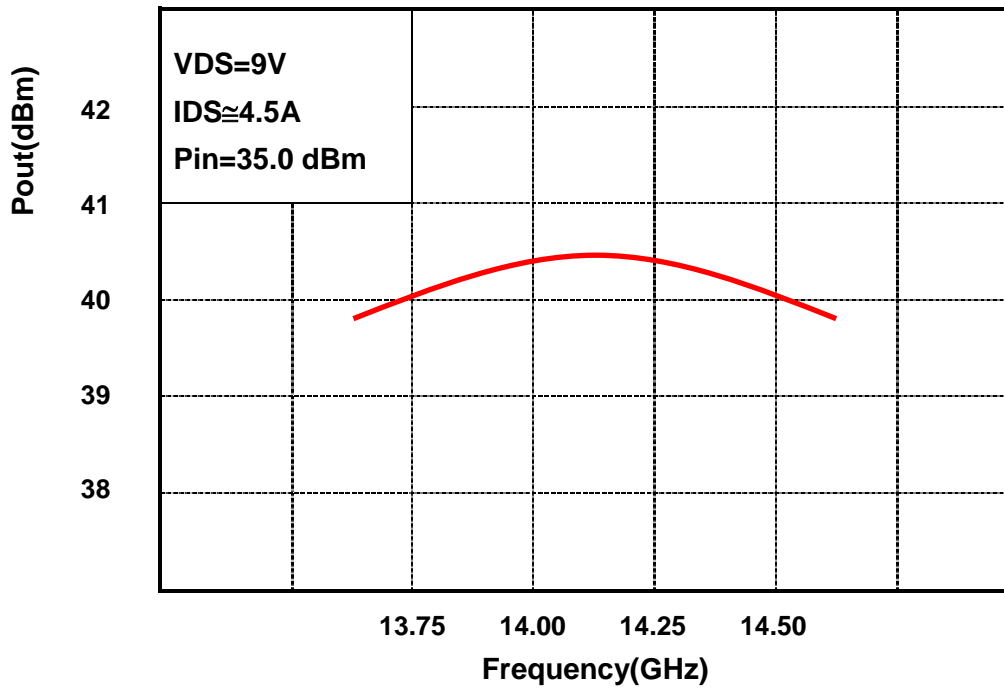


**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

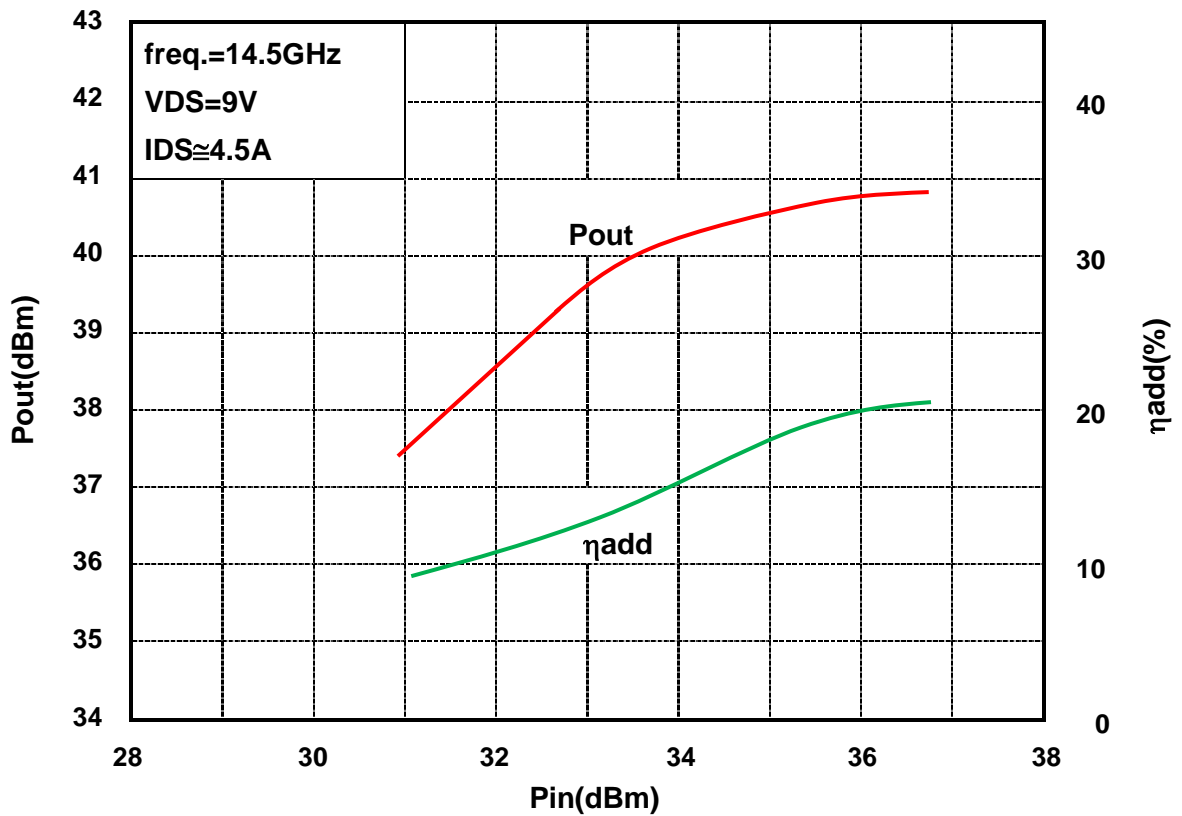
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

**RF PERFORMANCE**

**Output Power (Pout) vs. Frequency**



**Output Power(Pout) vs. Input Power(Pin)**



**Power Dissipation(PT) vs. Case Temperature(Tc)**

